



《风光欣》技术资料

S9014

NPN EPITAXIAL SILICON TRANSISTOR

FEATURES

Power dissipation

PCM : 0.2W (Tamb=25)

Collector current

ICM:0.1A

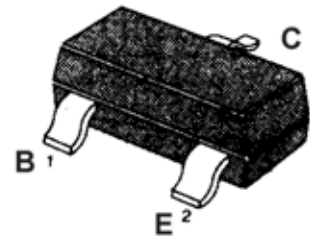
Collector-base Voltage

V(BR)CBO : 60V

Operating and storage junction temperature range

TJ,Tstg : -55 to+150

SOT-23



ELECTRICAL CHARACTERISTICS (TA=25)

Parameter	Symbol	Test conditons	MIN	MAX	UNIT
Collector -base breakdown voltage	V(BR)CBO	IC=100 μ A,IE=0	60		V
Collector-emitter breakdown Voltage	V(BR)CEO	IC=10mA,IB=0	50		V
Emitter-basebreakdown voltage	V(BR)EBO	IE=100 μ A,IB=0	5		V
Collector cut-off current	ICBO	VCE=60V,IE=0		0.1	μ A
Emitter cut-off current	IEBO	VEB=5V,IC=0		0.1	μ A
DC current gain	hFE	VCE=6V,IC=1mA	90	600	
Collector-emitter saturation voltage	VCEsat	IC=100mA,IB=5mA		0.3	V
Base-emitter saturation voltage	VBEsat	IC=100mA,IB=5mA		1	V
Base-emitter voltage	VBEF	VCE=6V,IE=10mA	0.55	0.65	V
Transition frequency	fT	VCE=6V,IC=1mA	250		MHZ

CLASSIFICATON OF hFE

RANK	L4	L5	L6	L7
RANGE	90-180	135-270	200-400	300-600